



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Features

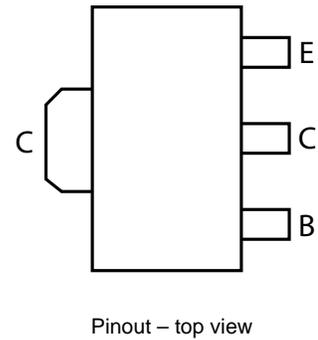
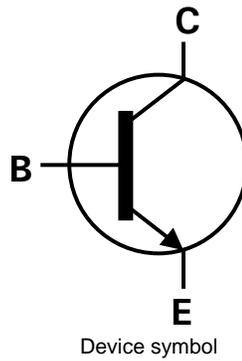
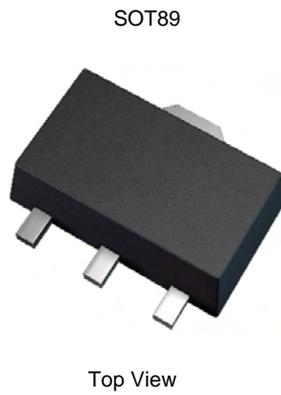
- $BV_{CEO} > 150V$
- $h_{FE} > 100$ for $I_C = 150mA$, $V_{CE} = 0.25V$
- $I_C (cont) = 1A$

Applications

- LED TV backlight

Mechanical Data

- Case: SOT-89
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.008 grams (Approximate)



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

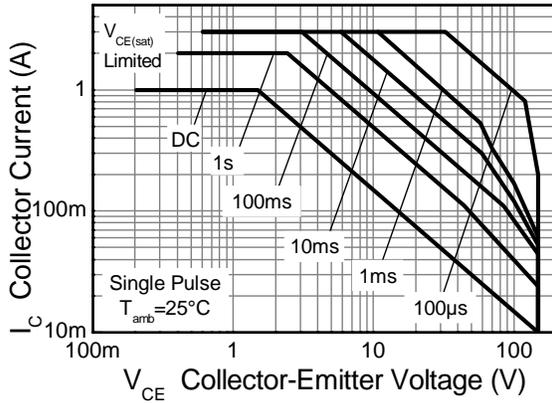
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	150	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	1	A
Peak Pulse Current (Note 4)	I_{CM}	3	A
Base Current	I_B	500	mA

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

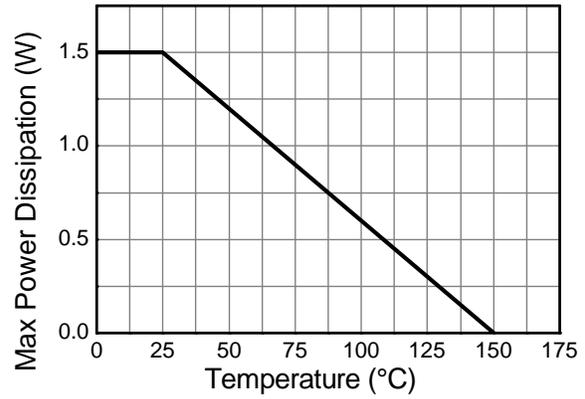
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_D	1.5	W
Thermal Resistance, Junction to Ambient (Note 3)	$R_{\theta JA}$	83	$^\circ\text{C/W}$
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	6.36	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 3. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions.
 4. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$.

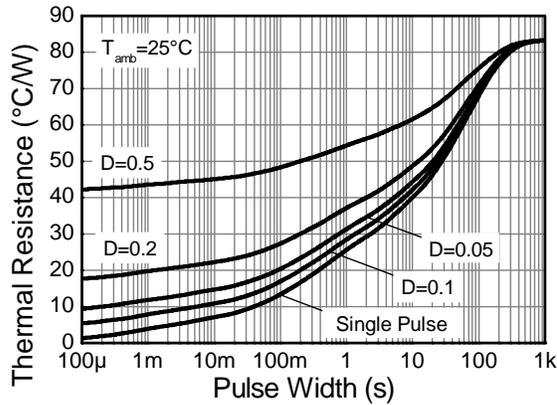
Thermal Characteristics and Derating information



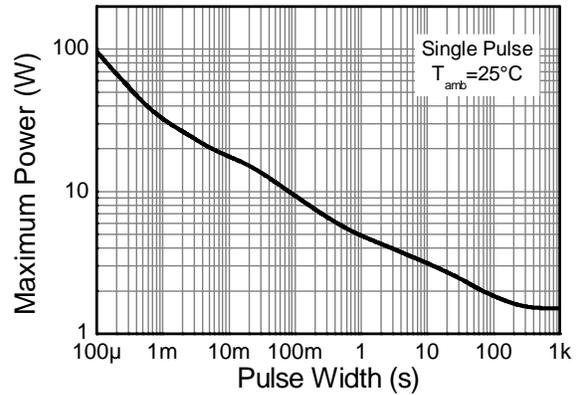
Safe Operating Area



Derating Curve



Transient Thermal Impedance



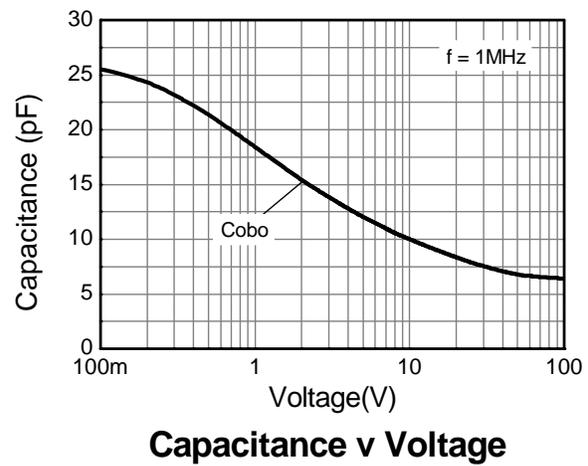
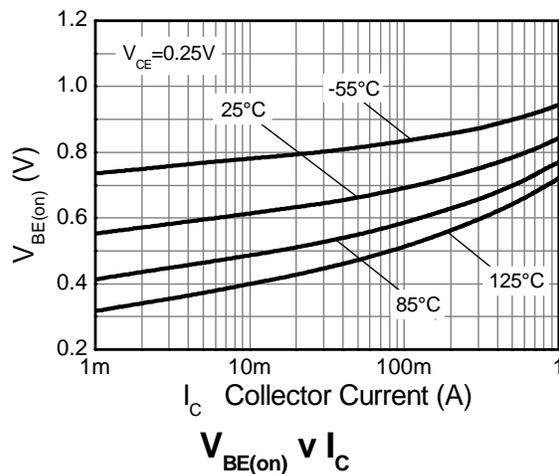
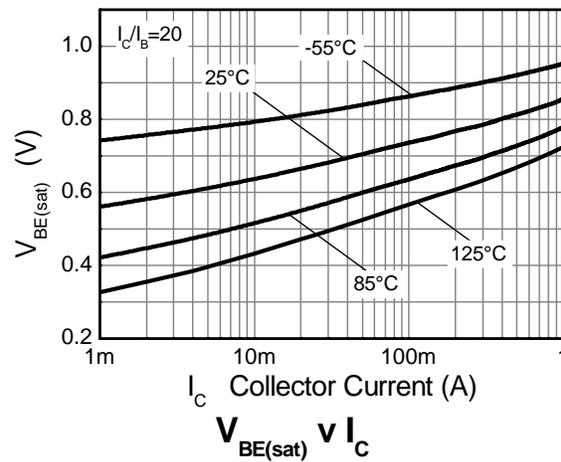
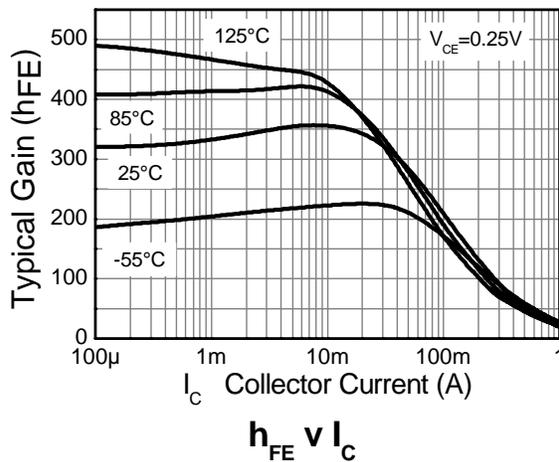
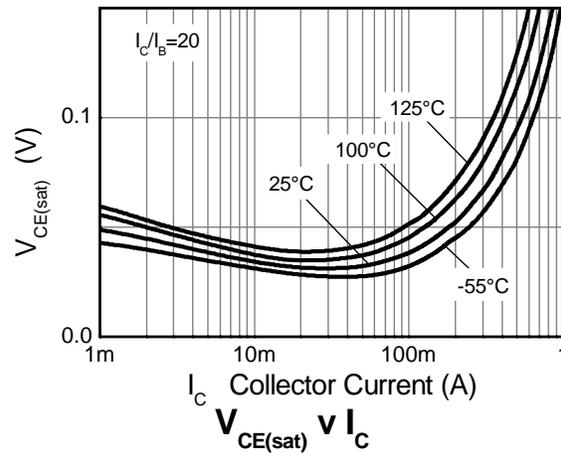
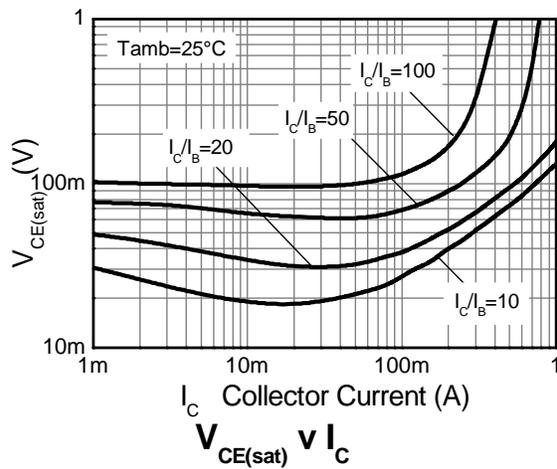
Pulse Power Dissipation

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

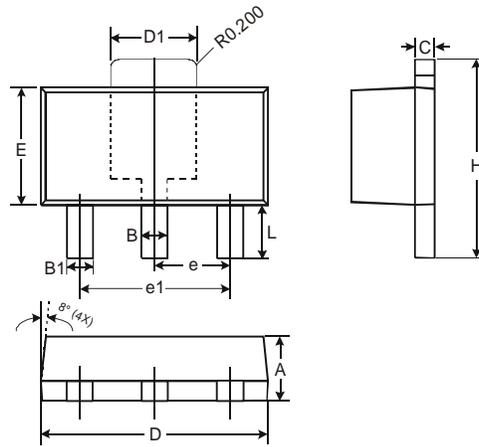
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	150	300	-	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 5)	BV_{CEO}	150	175	-	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.3	-	V	$I_E = 100\mu\text{A}$
Collector Cut-off Current	I_{CBO}	-	-	50	nA	$V_{CB} = 150\text{V}$
Emitter Cut-off Current	I_{EBO}	-	-	50	nA	$V_{EB} = 7\text{V}$
Static Forward Current Transfer Ratio (Note 5)	h_{FE}	200 60 100	450 180 150	- - -	-	$I_C = 30\text{mA}, V_{CE} = 5\text{V}$ $I_C = 85\text{mA}, V_{CE} = 0.20\text{V}$ $I_C = 150\text{mA}, V_{CE} = 0.25\text{V}$
Base-Emitter Turn-On Voltage (Note 5)	$V_{BE(on)}$	-	0.701	0.95	V	$I_C = 150\text{mA}, V_{CE} = 0.25\text{V}$
Output Capacitance	C_{OBO}	-	10	-	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Current Gain-Bandwidth Product	f_t	-	135	-	MHz	$V_{CB} = 10\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Delay Time	$t_{(d)}$	-	625	-	ns	$V_{CC} = 110\text{V}, I_C = 150\text{mA}, -I_{B2} = 1.5\text{mA}, V_{CE(ON)} = 0.25\text{V}$
Rise Time	$t_{(r)}$	-	562	-	ns	
Storage Time	$t_{(s)}$	-	2465	-	ns	
Fall Time	$t_{(f)}$	-	289	-	ns	
Storage Time	$t_{(s)}$	-	461	-	ns	
Fall Time	$t_{(f)}$	-	52	-	ns	$V_{CC} = 110\text{V}, I_C = 150\text{mA}, -I_{B2} = 1.5\text{mA}, V_{CE(ON)} = 4\text{V}$

 Notes: 5. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$

Typical Characteristics

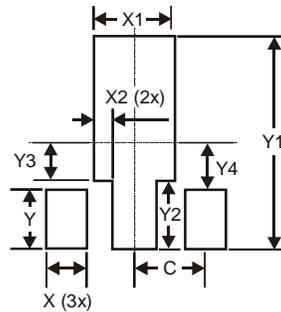


Package Outline Dimensions



SOT89-3L		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.43
D	4.40	4.60
D1	1.52	1.83
E	2.29	2.60
e	1.50 Typ	
e1	3.00 Typ	
H	3.94	4.25
L	0.89	1.20
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500